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Handbook of Nitride Semiconductors and Devices

Vol. 1: Materials Properties, Physics and Growth



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Contents

Preface XIII

Color Tables XXI

1	General Properties of Nitrides	1
	Introduction	1
1.1	Crystal Structure of Nitrides	1
1.2	Gallium Nitride	30
1.2.1	Chemical Properties of GaN	35
1.2.2	Mechanical Properties of GaN	35
1.2.3	Thermal Properties of GaN	47
1.3	Aluminum Nitride	62
1.3.1	Mechanical Properties of AlN	62
1.3.2	Thermal and Chemical Properties of AlN	66
1.3.3	Electrical Properties of AlN	69
1.3.4	Brief Optical Properties of AlN	71
1.4	Indium Nitride	75
1.4.1	Crystal Structure of InN	77
1.4.2	Mechanical Properties of InN	77
1.4.3	Thermal Properties of InN	79
1.4.4	Brief Electrical Properties of InN	81
1.4.5	Brief Optical Properties of InN	84
1.5	Ternary and Quaternary Alloys	89
1.5.1	AlGaN Alloy	90
1.5.2	InGaN Alloy	92
1.5.3	InAlN Alloy	97
1.5.4	InAlGaN Quaternary Alloy	99
1.5.5	Dilute GaAs(N)	105
	References	110

2	Electronic Band Structure and Polarization Effects	131
	Introduction	131
2.1	Band Structure Calculations	132
2.1.1	Plane Wave Expansion Method	134
2.1.2	Orthogonalized Plane Wave (OPW) Method	134
2.1.3	Pseudopotential Method	135
2.1.4	Augmented Plane Wave (APW) Method	135
2.1.5	Other Methods and a Review Pertinent to GaN	136
2.2	General Strain Considerations	154
2.3	Effect of Strain on the Band Structure of GaN	159
2.4	$k\cdot p$ Theory and the Quasi-Cubic Model	160
2.5	Quasi-Cubic Approximation	167
2.6	Temperature Dependence of Wurtzite GaN Bandgap	169
2.7	Sphalerite (Zinc blende) GaN	172
2.8	AlN	176
2.8.1	Wurtzite AlN	177
2.8.2	Zinc Blende AlN	183
2.9	InN	184
2.9.1	Wurtzitic InN	185
2.9.2	Zinc Blende InN	200
2.10	Band Parameters for Dilute Nitrides	202
2.10.1	GaAsN	205
2.10.2	InAsN	208
2.10.3	InPN	209
2.10.4	InSbN	209
2.10.5	GaPN	210
2.10.6	GaInAsN	210
2.10.7	GaInPN	212
2.10.8	GaAsSbN	212
2.11	Confined States	212
2.11.1	Conduction Band	216
2.11.2	Valence Band	224
2.11.3	Exciton Binding Energy in Quantum Wells	227
2.12	Polarization Effects	230
2.12.1	Piezoelectric Polarization	236
2.12.2	Spontaneous Polarization	241
2.12.3	Nonlinearity of Polarization	245
2.12.3.1	Origin of the Nonlinearity	250
2.12.3.2	Nonlinearities in Spontaneous Polarization	253
2.12.3.3	Nonlinearities in Piezoelectric Polarization	256
2.12.4	Polarization in Heterostructures	264
2.12.4.1	Ga-Polarity Single AlGaN/GaN Interface	272
2.12.4.2	Ga-Polarity Single $\text{Al}_x\text{In}_{1-x}\text{N}/\text{GaN}$ Interface	276
2.12.5	Polarization in Quantum Wells	278

2.12.5.1	Nonlinear Polarization in Quantum Wells	280
2.12.5.2	InGaN/GaN Quantum Wells	286
2.12.6	Effect of Dislocations on Piezoelectric Polarization	289
2.12.7	Thermal Mismatch Induced Strain	290
	References	299
3	Growth and Growth Methods for Nitride Semiconductors	323
	Introduction	323
3.1	Substrates for Nitride Epitaxy	324
3.1.1	Conventional Substrates	326
3.1.2	Compliant Substrates	327
3.1.3	van der Waals Substrates	328
3.2	A Primer on Conventional Substrates and their Preparation for Growth	329
3.2.1	GaAs	329
3.2.1.1	A Primer on GaAs	330
3.2.1.2	Surface Preparation of GaAs for Epitaxy	331
3.2.2	Si	332
3.2.2.1	A Primer on Si	332
3.2.2.2	Surface Preparation of Si for Epitaxy	333
3.2.3	SiC	334
3.2.3.1	A Primer on SiC	334
3.2.3.2	Surface Preparation of SiC for Epitaxy	338
3.2.4	Sapphire	342
3.2.4.1	A Primer on Sapphire	343
3.2.4.2	Surface Preparation of Sapphire for Epitaxy	346
3.2.5	ZnO	350
3.2.5.1	A Primer on ZnO	351
3.2.5.2	Substrate Preparation for Epitaxy	353
3.2.6	LiGaO ₂ and LiAlO ₂	355
3.2.6.1	LiGaO ₂ Substrates	355
3.2.6.2	LiAlO ₂ Substrates	358
3.2.7	AlN and GaN	359
3.2.7.1	Seedless Growth of GaN	362
3.2.7.1.1	Seedless Growth of GaN by High Nitrogen Pressure Solution Growth (HNPSG) for Substrates	362
3.2.7.1.2	Seeded Growth of GaN by HNPSG Method for Substrates	363
3.2.7.2	Pertinent Surfaces of GaN	365
3.2.7.3	GaN Surface Preparation for Epitaxy	369
3.2.8	Other Substrates	371
3.3	GaN Epitaxial Relationship to Substrates	372
3.3.1	Epitaxial Relationship of GaN and AlN with Sapphire	372
3.3.2	Epitaxial Relationship of GaN and AlN with SiC	381
3.3.3	Epitaxial Relationship of GaN and AlN with Si	381
3.3.4	Epitaxial Relationship of GaN with ZnO	381

3.3.5	Epitaxial Relationship of GaN with LiGaO ₂ and LiAlO ₂ and Perovskites	382
3.4	Nitride Growth Techniques	384
3.4.1	Vapor Phase Epitaxy	385
3.4.1.1	Hydride Vapor Phase Epitaxy	385
3.4.1.2	Organometallic Vapor Phase Epitaxy	393
3.4.1.3	Modeling of OMVPE Growth	398
3.4.1.3.1	Thermal Decomposition of GaN as it Relates to Growth	398
3.4.1.3.2	Ga and N Precursor Adsorption and Decomposition	400
3.4.1.3.3	Ga and N ₂ Desorption from the Surface	401
3.4.1.3.4	Ga and N Surface Diffusion	403
3.4.1.3.5	Kinetic Model: Balance Between Adsorption and Desorption	405
3.4.1.3.6	Comparison of Model with Growth Conditions for Surface Morphology	406
3.4.2	Molecular Beam Epitaxy	409
3.4.2.1	Adsorption	411
3.4.2.2	Desorption	412
3.4.2.3	Surface Diffusion	413
3.4.2.4	Incorporation	415
3.4.2.5	Decomposition	416
3.4.2.6	Reflection High-Energy Electron Diffraction	417
3.4.2.7	Plasma-Assisted MBE (PAMBE) or RF MBE, Primarily N Source	428
3.4.2.8	Reactive Ion MBE	435
3.4.2.9	Principles of RMBE and PAMBE Growth	436
3.4.2.9.1	Growth by RMBE	437
3.4.2.9.2	Growth by PAMBE	446
3.4.2.9.3	Which Species of N is Desirable?	451
3.4.2.9.4	The Effect of III/V Ratio and Substrate Temperature on Surface Morphology	455
3.5	The Art and Technology of Growth of Nitrides	462
3.5.1	Sources	467
3.5.1.1	HVPE Buffer Layers and Laser Lift-off	468
3.5.1.2	Benchmark HVPE Layers/Templates	472
3.5.2	Growth on GaAs Substrates	477
3.5.3	Growth on SiC: Nucleation Layers and GaN	479
3.5.3.1	Stacking and Interfacial Relationship	480
3.5.3.2	Nucleation Layers on SiC	482
3.5.3.2.1	High-Temperature AlN Nucleation Layers on SiC	486
3.5.3.2.2	Low-Temperature GaN Nucleation Layers on SiC	488
3.5.3.2.3	High-Temperature GaN Nucleation Layers on SiC	489
3.5.3.2.4	Alloy and Multiple Layer Nucleation Layers on SiC	491
3.5.3.2.5	Nucleation Layers on SiC by MBE	492
3.5.3.3	Substrate Misorientation and Domain Boundaries	495
3.5.3.4	Polarity of GaN on SiC	498

3.5.3.4.1	GaN Growth on SiC	499
3.5.3.5	Growth on Porous SiC	503
3.5.3.6	Zinc Blende Phase Growth	507
3.5.4	Growth on Si	507
3.5.5	Growth on Sapphire	512
3.5.5.1	OMVPE Low-Temperature Nucleation Buffer Layers	513
3.5.5.1.1	The Effect of V/III Ratio on Nucleation Buffer Layer	523
3.5.5.1.2	Effect of Epitaxial Growth Temperature	525
3.5.5.1.3	Effect of Process Pressure	525
3.5.5.2	Epitaxial Lateral Overgrowth	528
3.5.5.2.1	Selective Epitaxial Growth and Lateral Epitaxial Overgrowth with HVPE	537
3.5.5.2.2	Lateral Epitaxial Overgrowth on Si	539
3.5.5.2.3	Pendeo-Epitaxy	540
3.5.5.2.4	Pendeo-Epitaxy on SiC Substrates	542
3.5.5.2.5	Pendeo-Epitaxy on Silicon Substrates	544
3.5.5.2.6	Point Defect Distribution in ELO Grown GaN	558
3.5.5.3	Nanoheteroepitaxy and Nano-ELO	564
3.5.5.3.1	SiN and TiN Nanonets	569
3.5.5.4	Selective Growth Using W Masks	583
3.5.5.5	Low-Temperature Buffer Interlayer	584
3.5.6	Polarity and Surface Structure of GaN Layers, Particularly on Sapphire	586
3.5.6.1	MBE Buffer Layers	597
3.5.7	Growth on ZnO Substrates	598
3.5.8	Growth on LiGaO ₂ and LiAlO ₂ Substrates	603
3.5.9	Growth on GaN Templates	605
3.5.10	Growth on Spinel (MgAl ₂ O ₄)	611
3.5.11	Growth on Non <i>c</i> -Plane Substrates	611
3.5.11.1	The <i>a</i> -Plane GaN Growth	613
3.5.11.2	Epitaxial Lateral Overgrowth of <i>a</i> -plane GaN	616
3.5.11.3	The (1̄100) <i>m</i> -Plane GaN Growth	623
3.5.12	Growth of p-Type GaN	627
3.5.13	Growth of InN	629
3.5.14	Growth of AlN	638
3.5.14.1	Surface Reconstruction of AlN	642
3.5.15	Growth of Ternary and Quaternary Alloys	652
3.5.15.1	Growth of AlGaN	653
3.5.15.1.1	Growth of p-Type AlGaN	666
3.5.15.1.2	Ordering in AlGaN	668
3.5.15.2	Growth of InGaN	671
3.5.15.2.1	Doping of InGaN	678
3.5.15.2.2	Phase Separation in InGaN	679
3.5.15.2.3	Surface Reconstruction of InGaN	689
3.5.15.3	Growth of AlInN	695

3.5.15.3.1	Miscibility Gap in InAlN	697
3.5.15.4	InGaAlN Quaternary Alloy	699
3.5.16	Growth of Quantum Dots	706
3.5.16.1	Quantum Dots by MBE	711
3.5.16.2	Quantum Dots by OMVPE	719
3.5.16.3	Quantum Dots by Other Techniques	723
3.5.16.4	Preparation and Properties of Nanostructures	725
3.5.16.4.1	Approaches for Synthesis	726
3.5.16.4.2	Vapor Phase Growth	726
3.5.16.5	Nanowires and Longitudinal Heterostructures	737
3.5.16.5.1	Coaxial Heterostructures	755
3.5.16.5.2	Nanotubes	756
3.6	Concluding Remarks	759
	References	760
4	Extended and Point Defects, Doping, and Magnetism	817
	Introduction	817
4.1	A Primer on Extended Defects	818
4.1.1	Dislocations	819
4.1.1.1	Misfit Dislocations	822
4.1.1.2	Threading Dislocations	822
4.1.1.2.1	Edge Dislocations	824
4.1.1.2.2	Screw Dislocations	828
4.1.1.2.3	Mixed Dislocations	836
4.1.2	Nanopipes or Hollow Pipes	840
4.1.3	Planar Defects: Domain Boundaries	844
4.1.4	Stacking Faults	851
4.1.5	Grain Boundaries	862
4.1.6	Electronic Structure of Extended Defects	863
4.1.6.1	Open Core Versus Close Core in Screw Dislocations	865
4.1.6.2	Edge and Mixed Dislocations	866
4.1.6.3	Simple Stacking Faults: Electrical Nature	884
4.2	TEM Analysis of High Nitrogen Pressure (HNP) Solution Growth (HNPSG) and HVPE-Grown GaN	886
4.2.1	Extended Defect Characterization	887
4.2.2	Pyramidal Defects	894
4.2.3	V-Shaped Defects (Pits) in InGaN Multiple Quantum Wells (MQWs)	905
4.2.4	Structural Defect Analysis by Chemical Etch Delineation	905
4.2.5	Structural Defect Observations with Surface Probes	910
4.3	Point Defects and Autodoping	917
4.3.1	Theoretical Studies of Point Defects in GaN	919
4.3.1.1	Hydrogen and Impurity Trapping at Extended Defects	924
4.3.1.2	Vacancies, Antisites, Interstitials, and Complexes	928
4.3.1.2.1	Vacancies	929

4.3.1.2.2	Interstitials and Antisite Defects	934
4.3.2	Complexes	935
4.3.2.1	Shallow Donor – Gallium Vacancy Complexes	936
4.3.2.2	Shallow Acceptor – Nitrogen Vacancy Complexes	936
4.3.2.3	Hydrogen-Related Complexes	937
4.3.2.4	Other Complexes	938
4.4	Defect Analysis by Deep-Level Transient Spectroscopy	938
4.4.1	Basics of DLTS	939
4.4.2	Applications of DLTS to GaN	948
4.4.3	Dispersion in DLTS of GaN	970
4.4.4	Applications of DLTS to AlGaN, In-Doped AlGaN, and InAlN	977
4.5	Minority Carrier Lifetime	977
4.6	Positron Annihilation	982
4.6.1	Vacancy Defects and Doping in Epitaxial GaN	983
4.6.2	Growth Kinetics and Thermal Behavior of Vacancy Defects in GaN	993
4.7	Fourier Transform Infrared (FTIR), Electron Paramagnetic Resonance, and Optical Detection of Magnetic Resonance	998
4.8	Role of Hydrogen	1004
4.9	Intentional Doping	1006
4.9.1.1	Shallow Donors	1007
4.9.1.2	Substitutional Acceptors	1007
4.9.1.3	Isoelectronic Impurities	1009
4.9.2	n-Type Doping with Silicon, Germanium, Selenium, and Oxygen	1010
4.9.2.1	Si Doping	1010
4.9.2.2	Ge Doping	1011
4.9.2.3	Se Doping	1012
4.9.2.4	p-Type Doping	1013
4.9.3	p-Type Doping and Codoping with Donors and Acceptors	1014
4.9.3.1	Magnesium Doping	1014
4.9.3.1.1	Codoping for Improving p-Type Conductivity	1019
4.9.3.1.2	Use of Superlattices for Improving p-Type Conductivity	1032
4.9.3.1.3	Role of Hydrogen and Defects in Mg-Doped GaN	1034
4.9.3.2	Beryllium Doping	1038
4.9.3.3	Mercury Doping	1040
4.9.3.4	Carbon Doping	1040
4.9.3.5	Zinc Doping	1042
4.9.3.6	Calcium Doping	1042
4.9.3.7	Cadmium Doping	1043
4.9.3.8	Other Acceptors in GaN	1043
4.9.4	Doping with Isoelectronic Impurities	1044
4.9.4.1	Arsenic Doping	1044
4.9.4.2	Phosphorus Doping	1045
4.9.5	Doping with Rare Earths	1045
4.9.6	Doping with Transition Metals and Rare Earths	1046

4.9.6.1	Manganese Doping for Electronic Properties	1046
4.9.6.2	Other TM Doping for Electronic Properties	1060
4.9.6.3	General Remarks About Dilute Magnetic Semiconductors	1063
4.9.6.4	General Remarks About Spintronics	1075
4.9.6.5	Theoretical Aspects of Dilute Magnetic Semiconductor	1082
4.9.6.5.1	Carrier – Single Magnetic Ion Interaction	1084
4.9.6.5.2	Interaction Between Magnetic Ions	1086
4.9.6.5.3	Zener, Mean Field, RKKY, and Ab Initio Treatments	1089
4.9.6.6	A Primer to Magnetotransport Measurements	1103
4.9.6.6.1	Faraday Rotation, Kerr Effect, and Magnetic Circular Dichroism (MCD)	1104
4.9.6.7	II–VI and GaAs-Based Dilute Magnetic Semiconductors	1123
4.9.6.7.1	II–VI-Based Dilute Magnetic Semiconductors	1124
4.9.6.7.2	III–V-Based DMS: (GaMn)As	1133
4.9.7	Experimental Results of TM-Doped GaN	1141
4.9.7.1	Magnetotransport Properties TM-Doped GaN	1141
4.9.7.2	Magnetic Properties of Mn-Doped GaN	1143
4.9.7.3	Magneto-Optical Measurements in TM-Doped GaN	1146
4.9.8	Magnetic, Structural, Optical, and Electrical Properties of Cr-Doped GaN	1156
4.9.9	Other TM and Rare Earth Doped GaN:(Co, Fe, V, Gd, and so on)	1163
4.9.10	TM-Doped Nanostructures	1166
4.9.11	Applications of Ferromagnetism and Representative Devices	1167
4.9.12	Summarizing Comments on Ferromagnetism	1186
4.10	Ion Implantation and Diffusion for Doping	1188
4.11	Summary	1190
	References	1191

Index 1231

Appendix 1257